

ABSTRACT OF THE DISCLOSURE

A method for fabricating a transistor having a fully silicided gate is described. A silicon substrate with a semi-finished transistor formed thereon is provided, wherein the transistor comprises a gate dielectric film, a silicon gate, a cap layer on the silicon
5 gate, a spacer and a source/drain region. A raised source/drain is formed on the source/drain region, and then the cap layer is removed. Subsequently, a full silicidation process is performed to fully silicide the silicon gate.